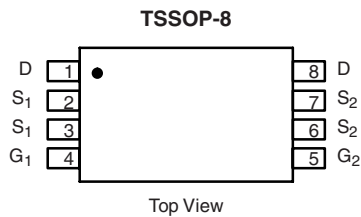


Dual N-Channel 2.5-V (G-S) MOSFET Common Drain, ESD Protection

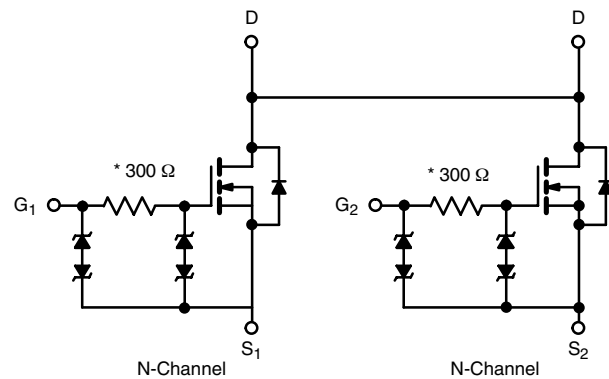
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.022 at $V_{GS} = 4.5$ V	6.5
	0.030 at $V_{GS} = 2.5$ V	5.5

FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFETs
- ESD Protected: 3000 V


RoHS*
COMPLIANT


Ordering Information: Si6968BEDQ-T1
Si6968BEDQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



* Typical value by design

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	20		V
Gate-Source Voltage	V_{GS}	± 12		
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	6.5	5.2
		$T_A = 70$ °C	5.5	3.5
Pulsed Drain Current	I_{DM}	30		A
Continuous Source Current (Diode Conduction) ^a	I_S	1.5	1.0	
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	1.5	1.0
		$T_A = 70$ °C	0.96	0.64
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	72	83
		Steady State	100	120
Maximum Junction-to-Foot (Drain)	R_{thJF}	55	70	°C/W

Notes:

a. Surface Mounted on FR4 board, $t \leq 10$ s.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

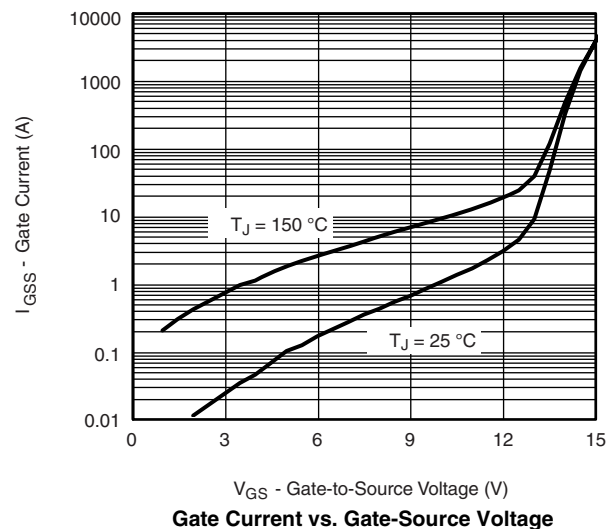
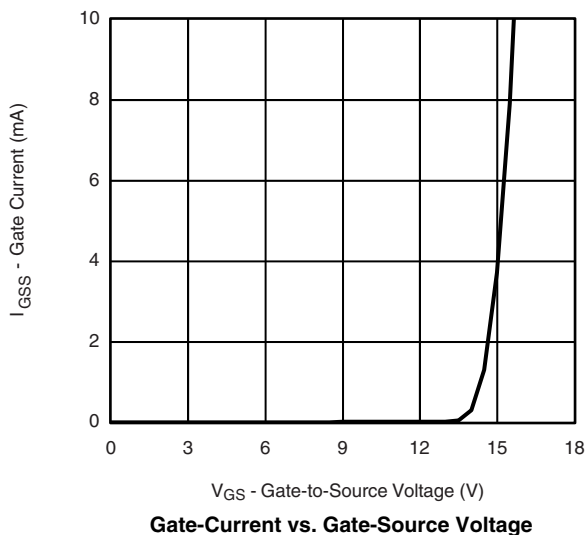
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.6		1.6	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			± 200	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			25	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = 4.5\text{ V}$	30			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 6.5\text{ A}$		0.0165	0.022	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 5.5\text{ A}$		0.023	0.030	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 6.5\text{ A}$		30		S
Diode Forward Voltage ^b	V_{SD}	$I_S = 1.5\text{ A}, V_{GS} = 0\text{ V}$		0.71	1.2	V
Dynamic^a						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 6.5\text{ A}$		12	18	nC
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			3.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 6\text{ }\Omega$		245	365	ns
Rise Time	t_r			330	495	
Turn-Off Delay Time	$t_{d(off)}$			860	1300	
Fall Time	t_f			510	765	

Notes:

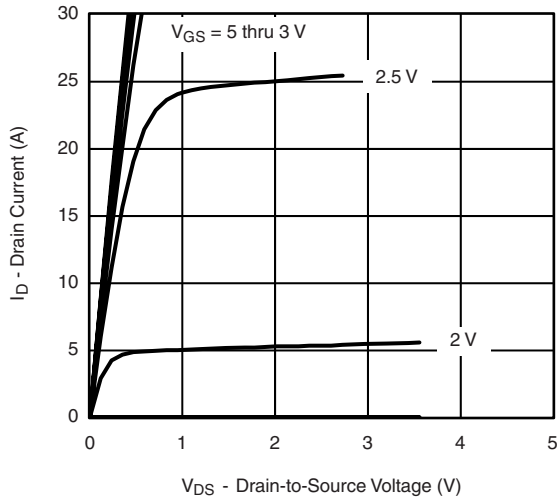
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

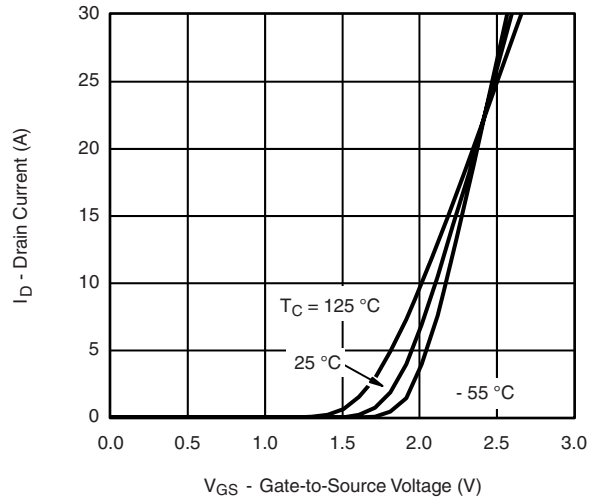
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



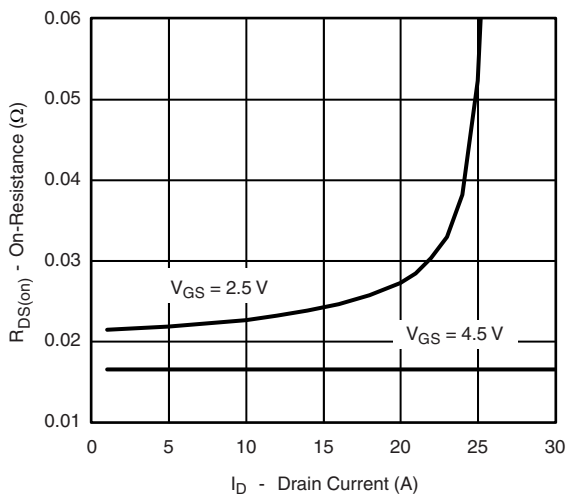
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



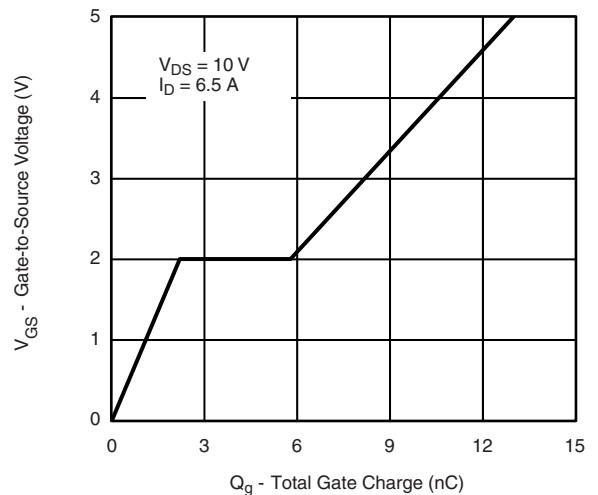
Output Characteristics



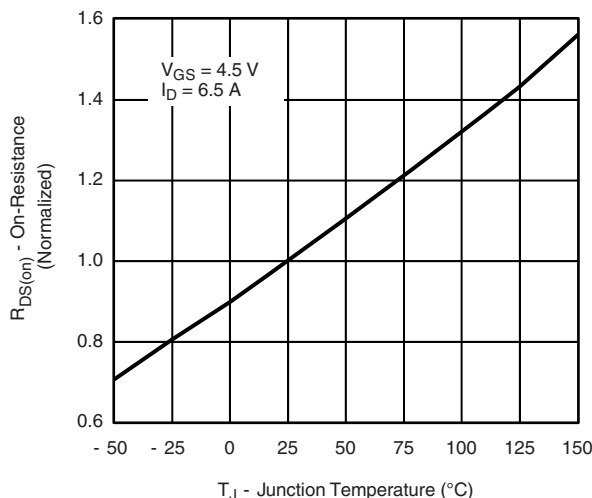
Transfer Characteristics



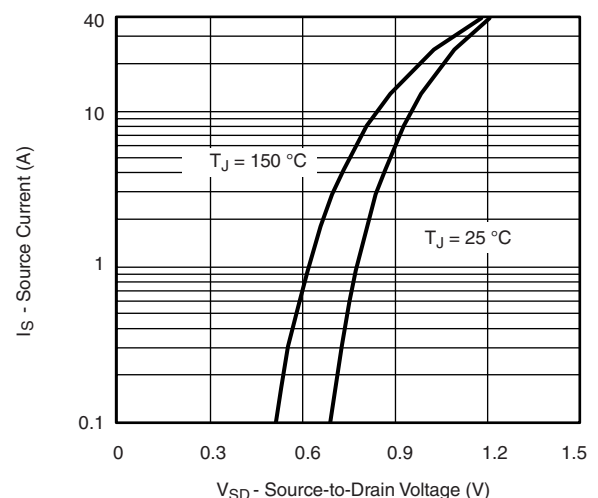
On-Resistance vs. Drain Current



Gate Charge

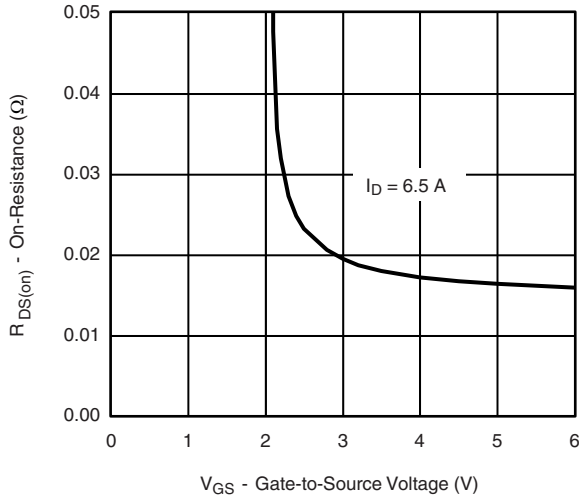


On-Resistance vs. Junction Temperature

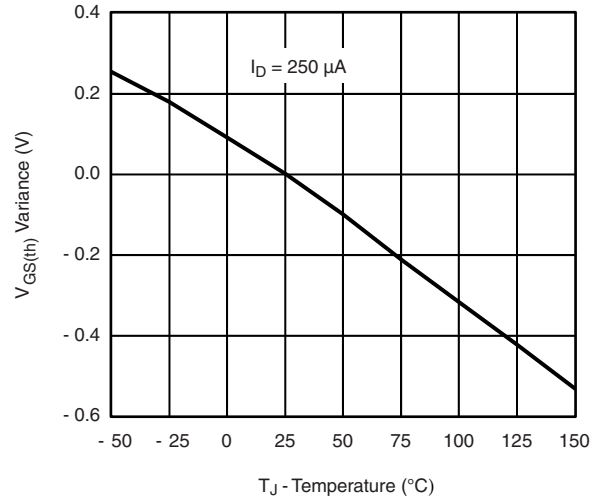


Source-Drain Diode Forward Voltage

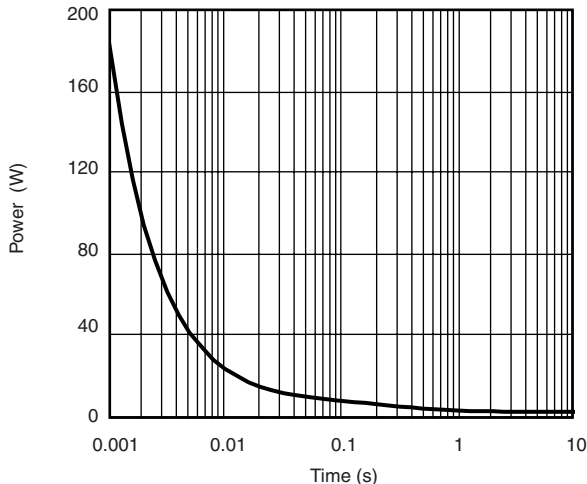
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



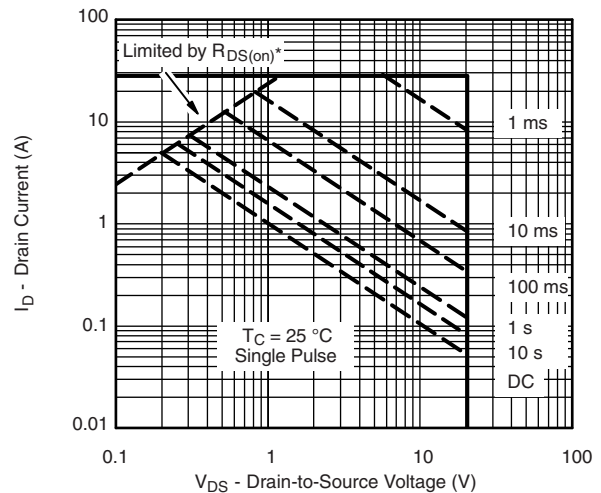
On-Resistance vs. Gate-to-Source Voltage



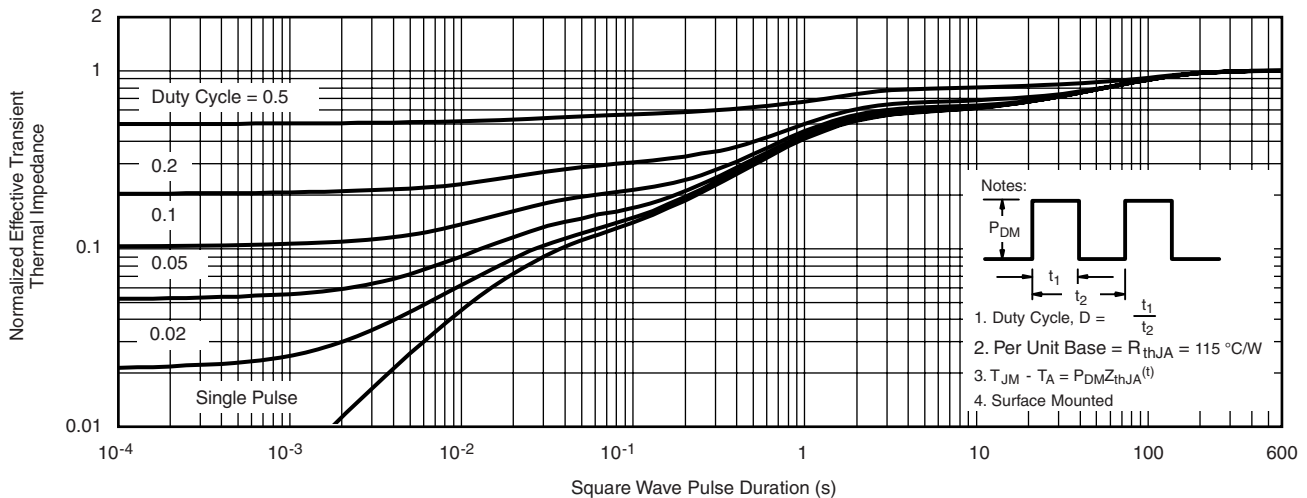
Threshold Voltage



Single Pulse Power

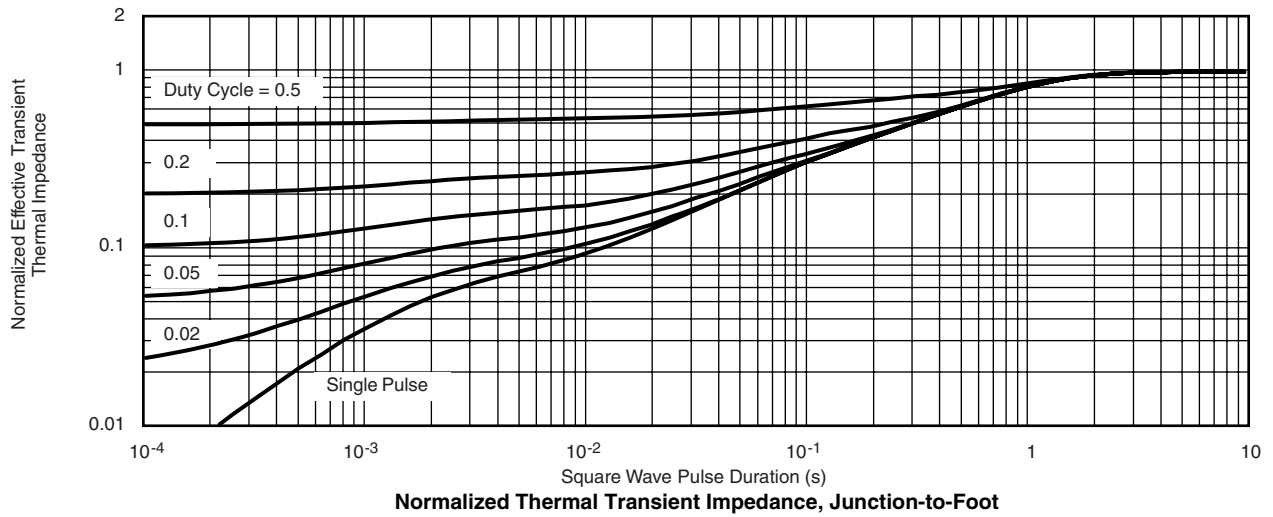


Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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